

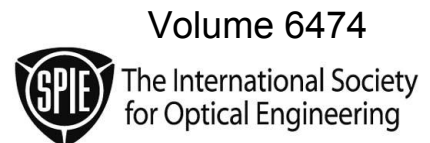
PROCEEDINGS OF SPIE

Zinc Oxide Materials and Devices II

**Ferechteh Hosseini Teherani
Cole W. Litton**
Editors

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